

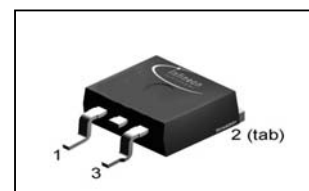
## 2<sup>nd</sup> Generation thinQ!<sup>TM</sup> SiC Schottky Diode

### Features

- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery/ No forward recovery
- No temperature influence on the switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Breakdown voltage tested at 5mA<sup>2)</sup>

### Product Summary

$V_{DC}$	600	V
$Q_c$	15	nC
$I_F$	6	A

**D<sup>2</sup>PAK**


### thinQ! 2G Diode designed for fast switching applications like:

- CCM PFC
- Motor Drives

Type	Package	Marking	Pin 2	Pin 3
IDB06S60C	D <sup>2</sup> PAK	D06S60C	C	A

### Maximum ratings, at $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous forward current	$I_F$	$T_C < 135\text{ }^\circ\text{C}$	6	A
RMS forward current	$I_{F,RMS}$	$f=50\text{ Hz}$	9	
Surge non-repetitive forward current, sine halfwave	$I_{F,SM}$	$T_C=25\text{ }^\circ\text{C}$ , $t_p=10\text{ ms}$	46	
Repetitive peak forward current	$I_{F,RM}$	$T_j=150\text{ }^\circ\text{C}$ , $T_C=100\text{ }^\circ\text{C}$ , $D=0.1$	24	
Non-repetitive peak forward current	$I_{F,max}$	$T_C=25\text{ }^\circ\text{C}$ , $t_p=10\text{ }\mu\text{s}$	210	
$i^2t$ value	$\int i^2 dt$	$T_C=25\text{ }^\circ\text{C}$ , $t_p=10\text{ ms}$	10	A <sup>2</sup> s
Repetitive peak reverse voltage	$V_{RRM}$		600	V
Diode ruggedness $dv/dt$	$dv/dt$	$V_R=0\dots 480\text{V}$	50	V/ns
Power dissipation	$P_{tot}$	$T_C=25\text{ }^\circ\text{C}$	52	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 175	$^\circ\text{C}$

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - case	$R_{thJC}$		-	-	2.9	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	SMD version, device on PCB, minimal Footprint	-	-	62	
		SMD version, device on PCB, 6 cm <sup>2</sup> cooling area <sup>3)</sup>	-	35	-	
Soldering temperature, reflowsoldering @ 10sec	$T_{sold}$	reflow MSL1	-	-	260	°C

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

DC blocking voltage	$V_{DC}$	$I_R=0.08\text{ mA}$	600	-	-	V
Diode forward voltage	$V_F$	$I_F=6\text{ A}, T_j=25\text{ °C}$	-	1.5	1.7	
		$I_F=6\text{ A}, T_j=150\text{ °C}$	-	1.7	2.1	
Reverse current	$I_R$	$V_R=600\text{ V}, T_j=25\text{ °C}$	-	0.7	80	µA
		$V_R=600\text{ V}, T_j=150\text{ °C}$	-	3	800	

**AC characteristics**

Total capacitive charge	$Q_c$	$V_R=400\text{ V}, I_F \leq I_{F,max}, di_F/dt=200\text{ A}/\mu\text{s}, T_j=150\text{ °C}$	-	15	-	nC
Switching time <sup>4)</sup>	$t_c$	$T_j=150\text{ °C}$	-	-	<10	ns
Total capacitance	$C$	$V_R=1\text{ V}, f=1\text{ MHz}$	-	280	-	pF
		$V_R=300\text{ V}, f=1\text{ MHz}$	-	35	-	
		$V_R=600\text{ V}, f=1\text{ MHz}$	-	35	-	

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> All devices tested under avalanche conditions, for a time periode of 5ms at 5mA.

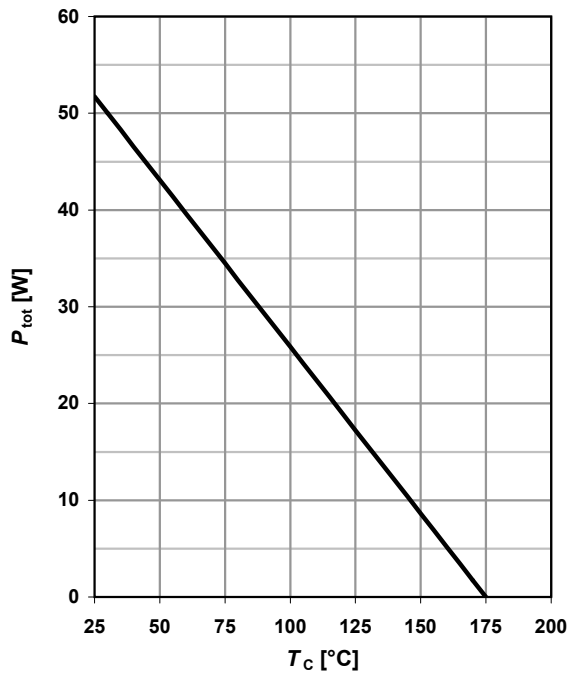
<sup>3)</sup> Device on 40mm\*40mm\*1.5mm epox PCB FR4 with 6cm<sup>2</sup> (one layer, 70µm thick) copper area for drain connection. PCB is vertikal with out blown air.

<sup>4)</sup>  $t_c$  is the time constant for the capacitive displacement current waveform (independent from  $T_j, I_{LOAD}$  and  $di/dt$ ), different from  $t_{rr}$ , which is dependent on  $T_j, I_{LOAD}, di/dt$ . No reverse recovery time constant  $t_{rr}$  due to absence of minority carrier injection.

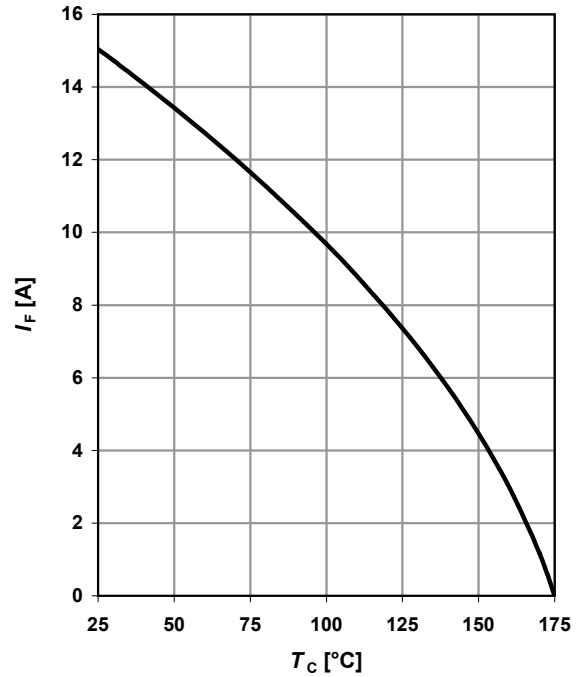
<sup>5)</sup> Only capacitive charge occuring, guaranteed by design.

**1 Power dissipation**

$$P_{\text{tot}} = f(T_C)$$

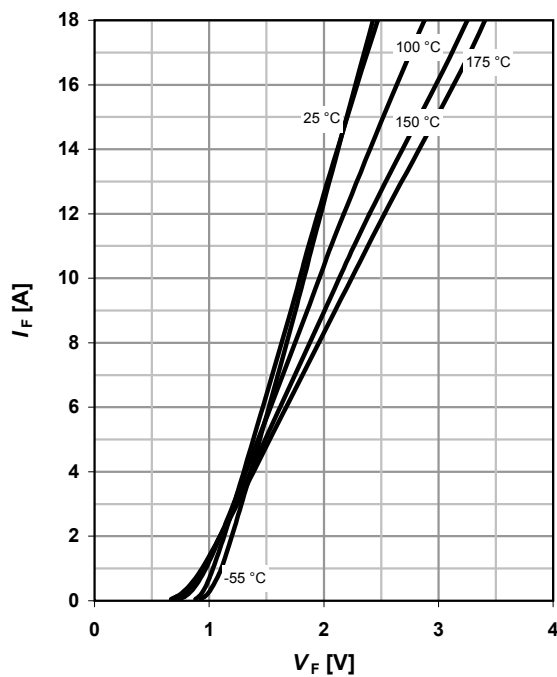

**2 Diode forward current**

$$I_F = f(T_C); T_j \leq 175 \text{ °C}$$

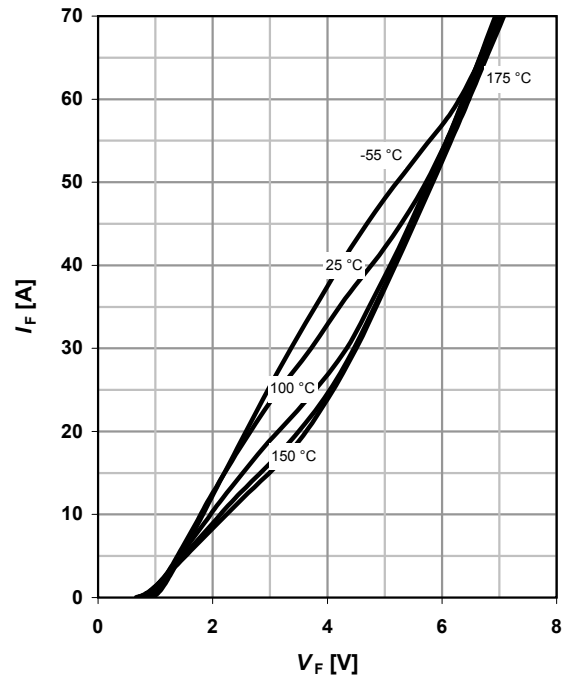

**3 Typ. forward characteristic**

$$I_F = f(V_F); t_p = 400 \text{ } \mu\text{s}$$

parameter:  $T_j$

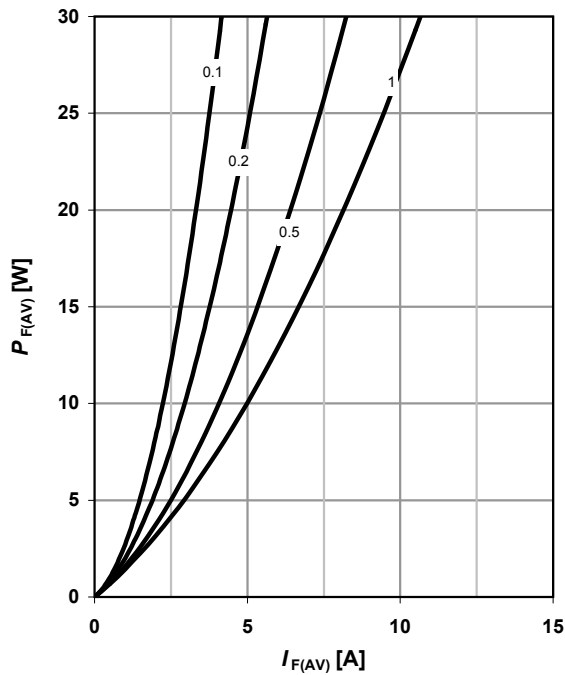

**4 Typ. forward characteristic in surge current mode**

$$I_F = f(V_F); t_p = 400 \text{ } \mu\text{s}; \text{ parameter } T_j$$



**5 Typ. forward power dissipation vs. average forward current**

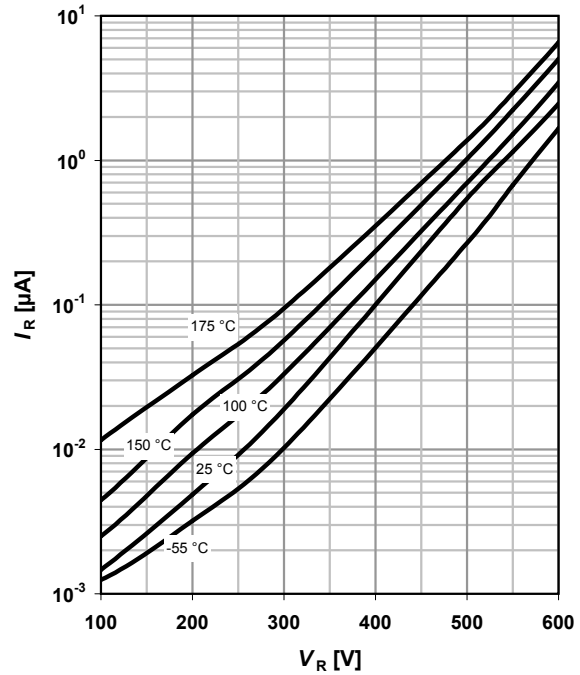
$$P_{F(AV)} = f(I_F), T_C = 100\text{ }^\circ\text{C}, \text{ parameter: } D = t_p/T$$



**6 Typ. reverse current vs. reverse voltage**

$$I_R = f(V_R)$$

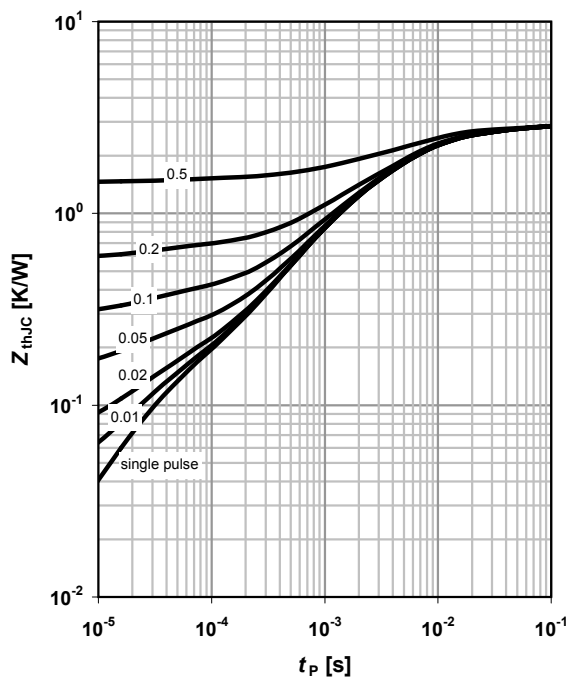
parameter:  $T_j$



**7 Transient thermal impedance**

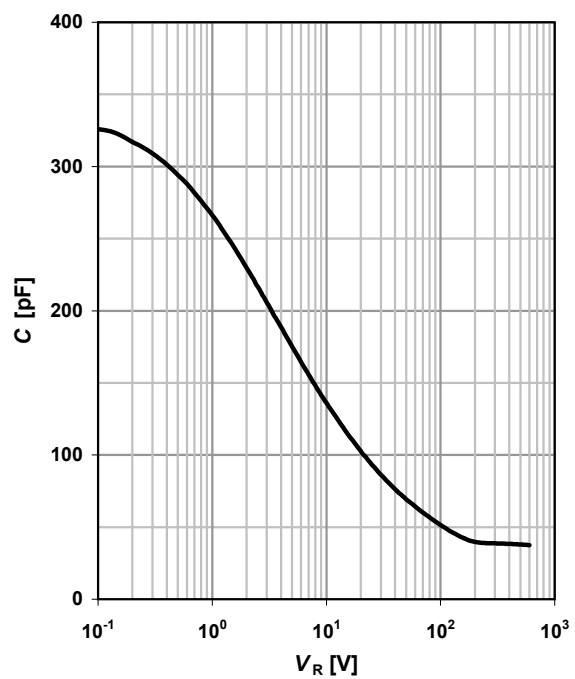
$$Z_{thJC} = f(t_p)$$

parameter:  $D = t_p/T$



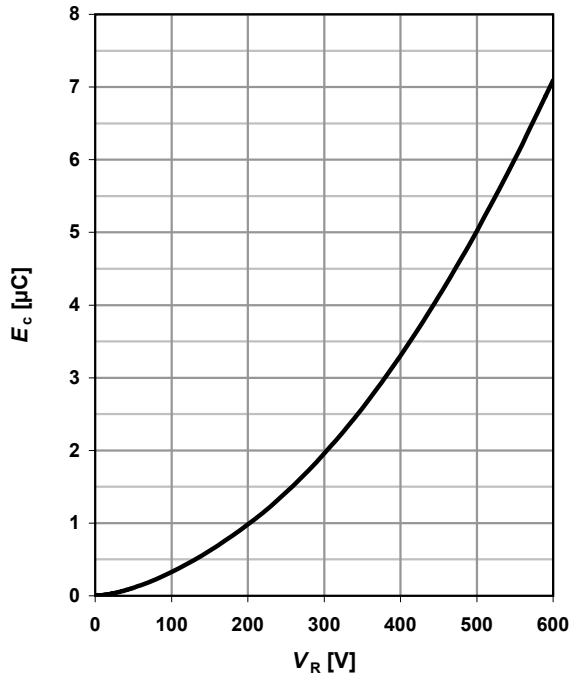
**8 Typ. capacitance vs. reverse voltage**

$$C = f(V_R); T_C = 25\text{ }^\circ\text{C}, f = 1\text{ MHz}$$



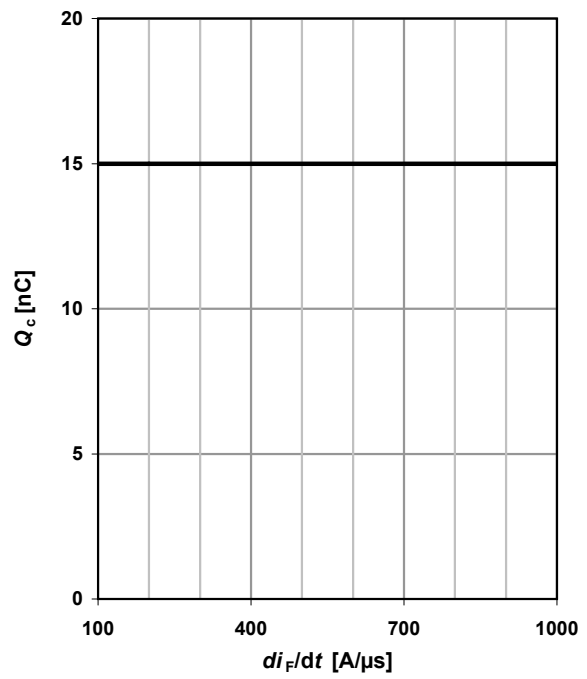
9 Typ. C stored energy

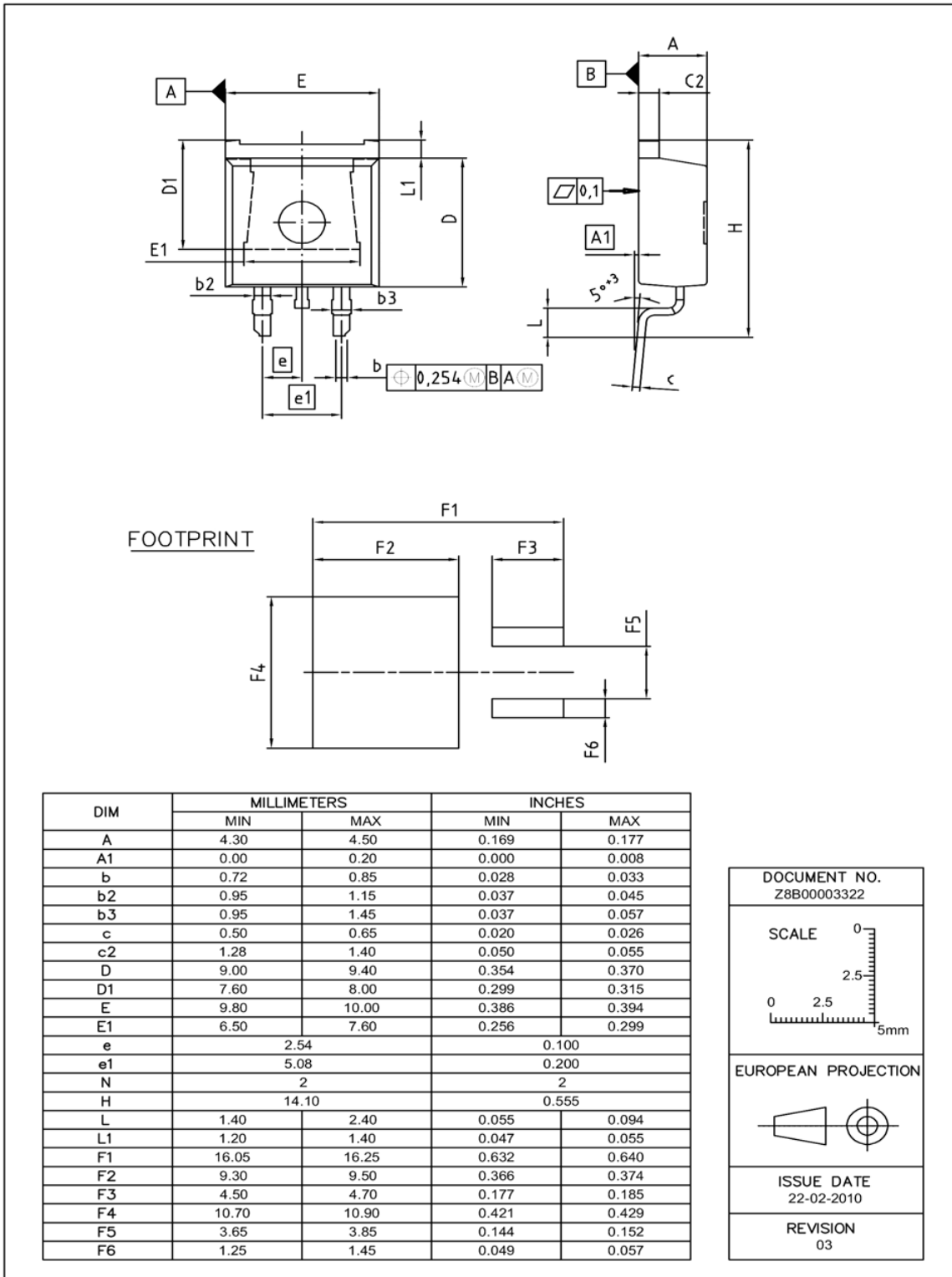
$$E_C = f(V_R)$$



10 Typ. capacitance charge vs. current slope

$$Q_C = f(di_F/dt)^{0.5}; T_j = 150\text{ °C}; I_F \leq I_{F,max}$$



**PG-TO220-3-45 (D2Pak): Outline**


Dimensions in mm/inches

**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**  
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